

MMG75HB060B6EN

600V 75A IGBT Module

February 2017

Version 2

RoHS Compliant

PRODUCT FEATURES

¶ IGBT³ CHIP(Trench+Field Stop technology)8(ION)-10.4(S)]TJ ET 30.84 541.28 78.24 1.08 re f 33.3(4 06637High s) -32(hor)8(t)79.7 ciGrcuit

¶ Free wheeling diodes with fast and soft reverse recovery

¶ CMI

APPLICATIONS

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NTC CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise specified)K

Unit
K
K

Unit

V
Nm
Nm
g

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$I_c(A)$

$E_{on}E_{off}(mJ)$

$V_{GE} \text{ \AA V \AA}$

Figure 3. Typical Transfer characteristics IGBT-inverter

$R_g \text{ \AA \AA}$

Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

μ

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$I_F(A)$

$E_{REC}(mJ)$

$V_F(V)$

$R_g \text{ \AA } \text{ \AA}$

Figure 14. Circuit Diagram

Dimensions in (mm)
Figure 15. Package Outline